

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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LOW V_{CE(SAT)} PNP SURFACE MOUNT TRANSISTOR

Features

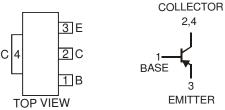
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DXT651)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)







Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Collector Current	I _{CM}	-6	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P_{D}	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

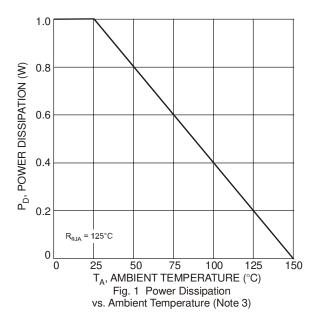
- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

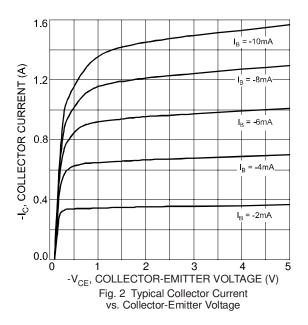


Electrical Characteristics @TA = 25°C unless otherwise specified

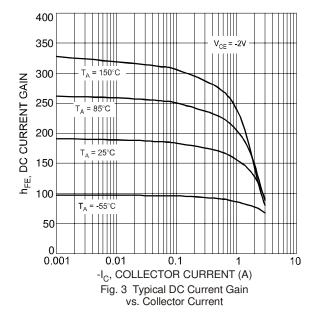
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-80	_		V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	-0.1 -10	μ Α μ Α	V _{CB} = -60V, I _E = 0 V _{CB} = -60V, I _E = 0, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	_	_	-0.1	μΑ	$V_{EB} = -4V, I_C = 0$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.08 -0.2	-0.3 -0.6	٧	$I_C = -1A$, $I_B = -100mA$ $I_C = -3A$, $I_B = -300mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	-0.9	-1.25	V	I _C = -1A, I _B = -100mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	-0.8	-1	V	$V_{CE} = -2V, I_{C} = -1A$
DC Current Gain	h _{FE}	70 100 80 40	200 180 160 140	300 — —		V _{CE} = -2V, I _C = -50mA V _{CE} = -2V, I _C = -500mA V _{CE} = -2V, I _C = -1A V _{CE} = -2V, I _C = -2A
AC CHARACTERISTICS						
Transition Frequency	f⊤	100	145	_	MHz	$V_{CE} = -10V$, $I_{C} = -50mA$, $f = 100MHz$
Output Capacitance	C_{obo}		_	30	рF	$V_{CB} = -10V$, $f = 1MHz$
Switching Times	t _{on} t _{off}		45 200		ns ns	$I_{C} = -500 \text{mA}, V_{CC} = -10 \text{V}$ $I_{B1} = I_{B2} = -50 \text{mA}$

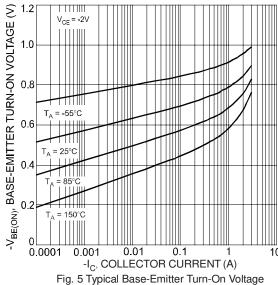
Notes: 4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

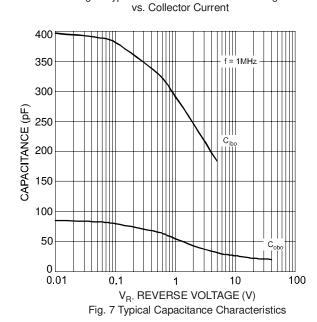












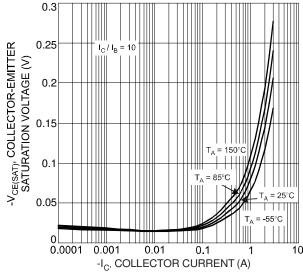


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

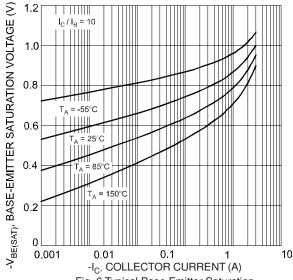


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

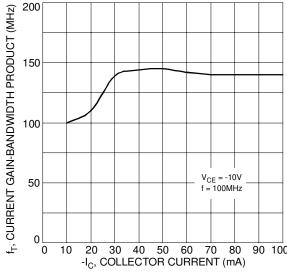


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

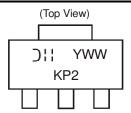


Ordering Information (Note 5)

Device	Packaging	Shipping
DXT751-13	SOT89-3L	2500/Tape & Reel

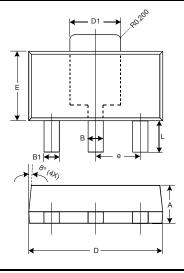
5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

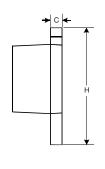
Marking Information



KP2 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

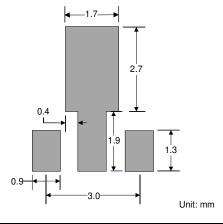
Package Outline Dimensions





SOT89-3L						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.45	0.55	0.50			
B1	0.37	0.47	0.42			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.50	1.70	1.60			
Е	2.40	2.60	2.50			
е	-		1.50			
Н	3.95	4.25	4.10			
L	0.90	1.20	1.05			
All Dimensions in mm						

Suggested Pad Layout



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